

General Description

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

Features

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity

GreenMOS[®]



Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

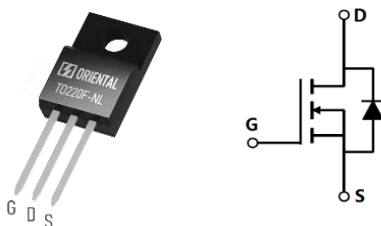
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	650	V
$I_{D, pulse}$	75	A
$R_{DS(ON)}, max @ V_{GS}=10V$	125	m Ω
Q_g	41.9	nC
PD	34	W

Marking Information

Product Name	Package	Marking
OSG65R125FF_NB	TO220F-NL	OSG65R125F

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^\circ\text{C}$	I_D	25	A
Continuous drain current ¹⁾ , $T_C=100^\circ\text{C}$		16	
Pulsed drain current ²⁾ , $T_C=25^\circ\text{C}$	$I_{D, pulse}$	75	A
Continuous diode forward current ¹⁾ , $T_C=25^\circ\text{C}$	I_S	25	A
Diode pulsed current ²⁾ , $T_C=25^\circ\text{C}$	$I_{S, pulse}$	75	A
Power dissipation ³⁾ , $T_C=25^\circ\text{C}$	P_D	34	W
Single pulsed avalanche energy ⁴⁾	E_{AS}	730	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$, $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	3.7	$^\circ\text{C/W}$
Thermal resistance, junction-ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$

Electrical Characteristics at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	650			V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.9		3.9	V	$V_{DS}=V_{GS}$, $I_D=1\text{ mA}$
Drain-source on-state resistance	$R_{DS(ON)}$		0.115	0.125	Ω	$V_{GS}=10\text{ V}$, $I_D=12.5\text{ A}$
			0.278			$V_{GS}=10\text{ V}$, $I_D=12.5\text{ A}$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=650\text{ V}$, $V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		2390.8		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		154.1		pF	
Reverse transfer capacitance	C_{rss}		3.9		pF	
Turn-on delay time	$t_{d(on)}$		32.4		ns	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $R_G=2\ \Omega$, $I_D=12.5\text{ A}$
Rise time	t_r		30.8		ns	
Turn-off delay time	$t_{d(off)}$		63.2		ns	
Fall time	t_f		4.9		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		41.9		nC	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $I_D=12.5\text{ A}$
Gate-source charge	Q_{gs}		10.4		nC	
Gate-drain charge	Q_{gd}		14.1		nC	
Gate plateau voltage	$V_{plateau}$		5.7		V	

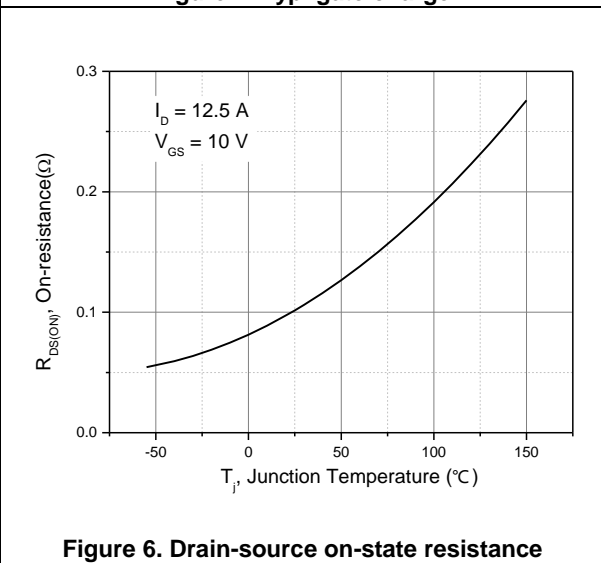
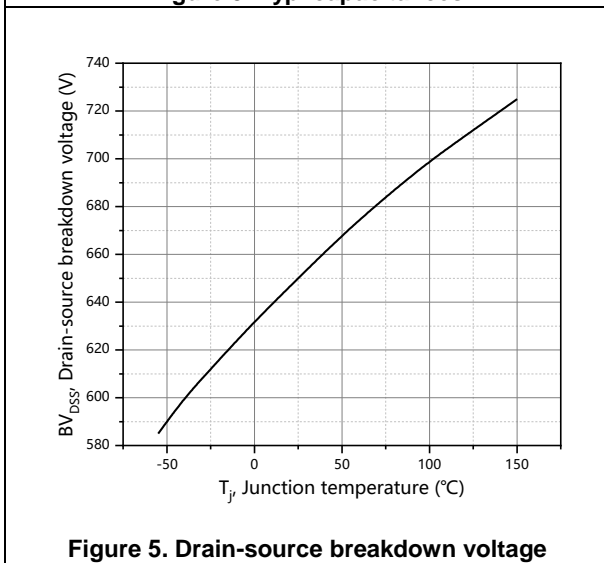
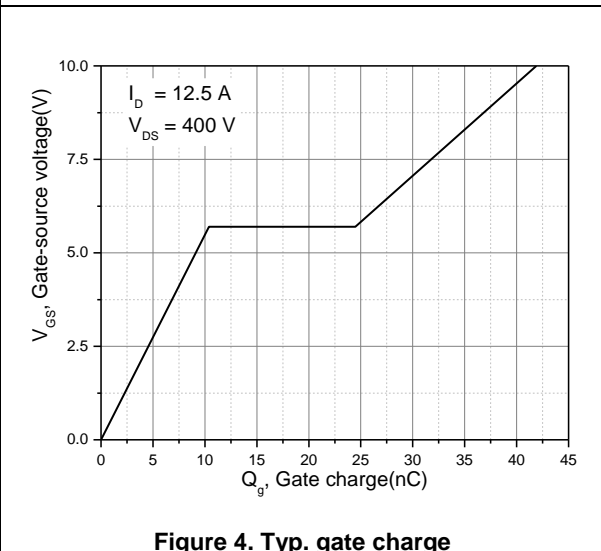
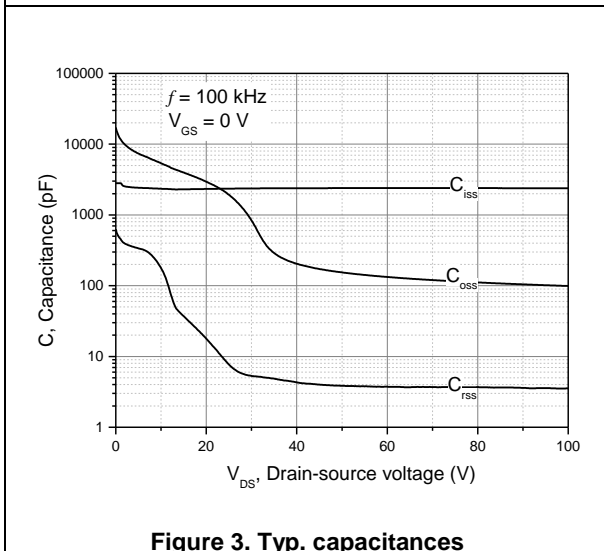
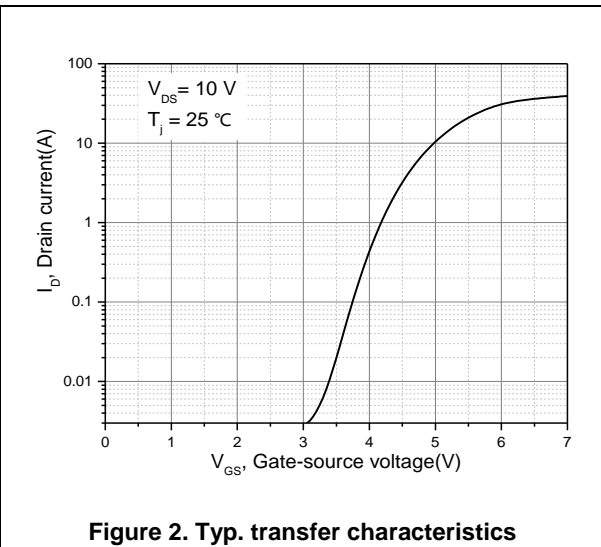
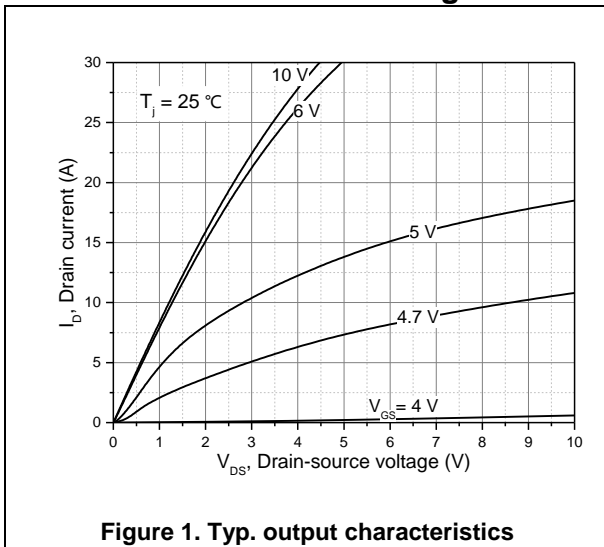
Body Diode Characteristics

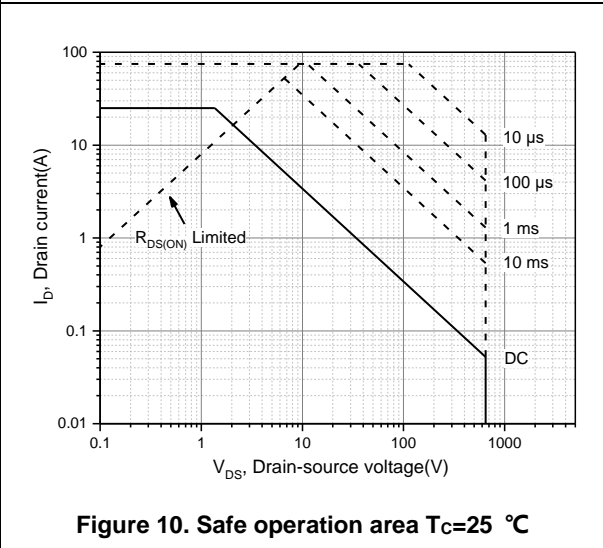
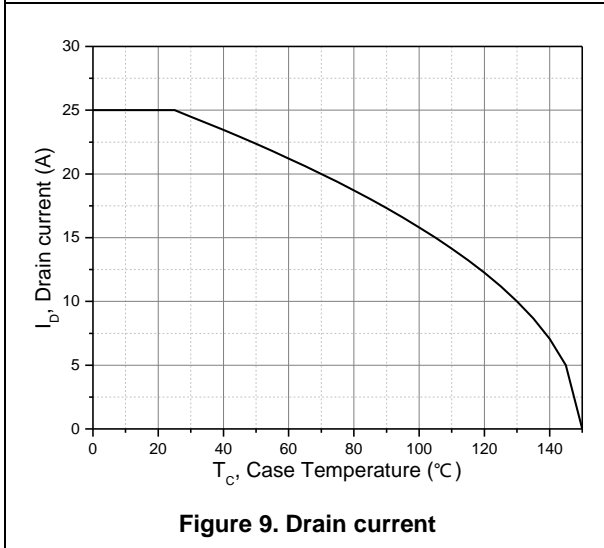
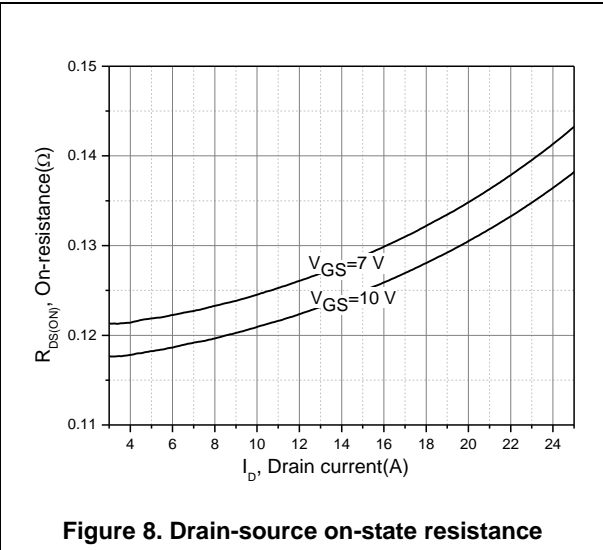
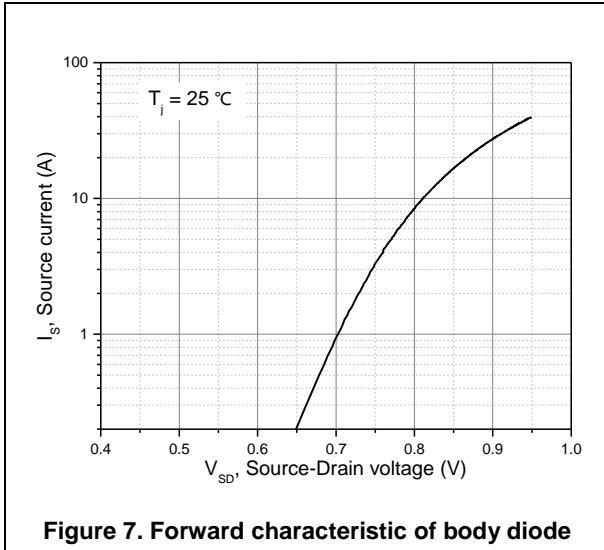
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.4	V	$I_S=25\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		365.2		ns	$I_S=12.5\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		4.7		μC	
Peak reverse recovery current	I_{rrm}		24.9		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=75\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams





Test circuits and waveforms

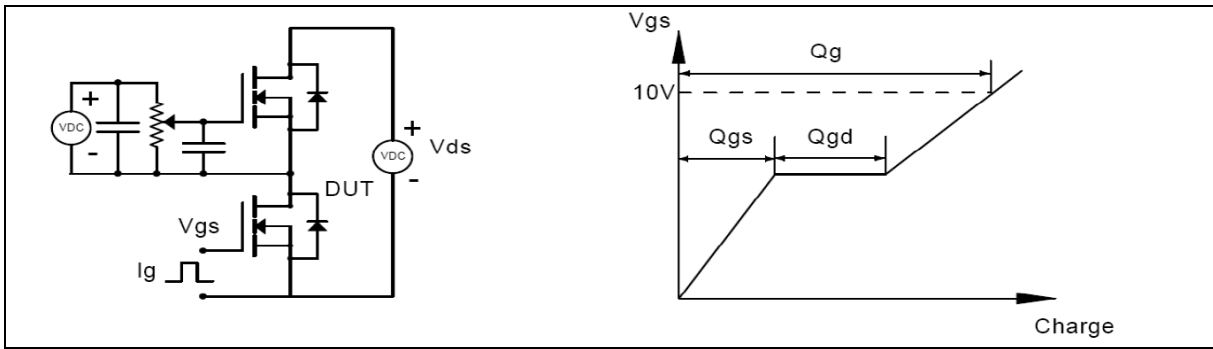


Figure 1. Gate charge test circuit & waveform

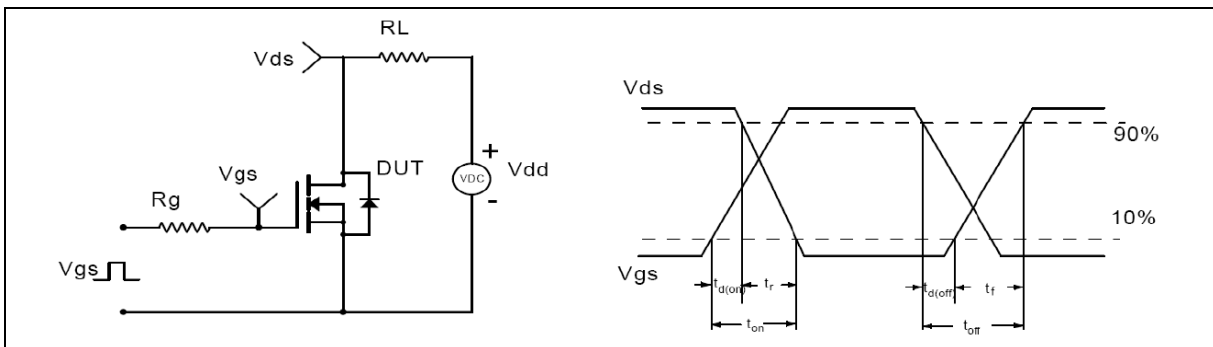


Figure 2. Switching time test circuit & waveforms

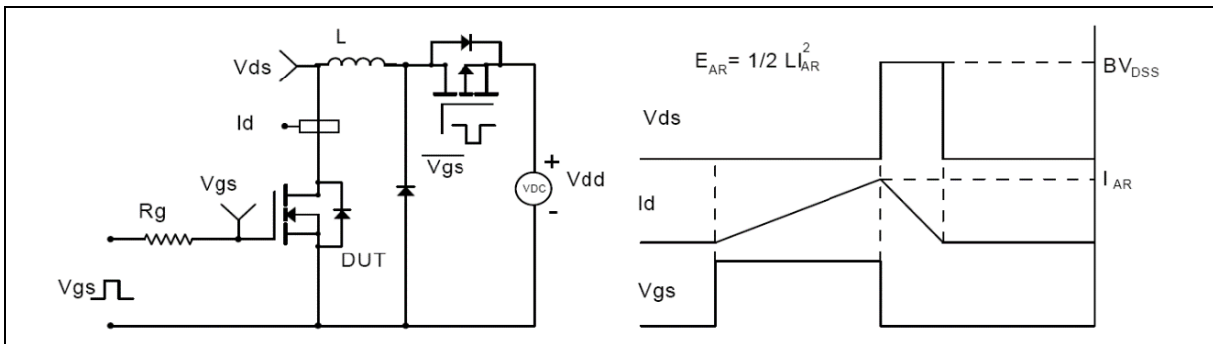


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

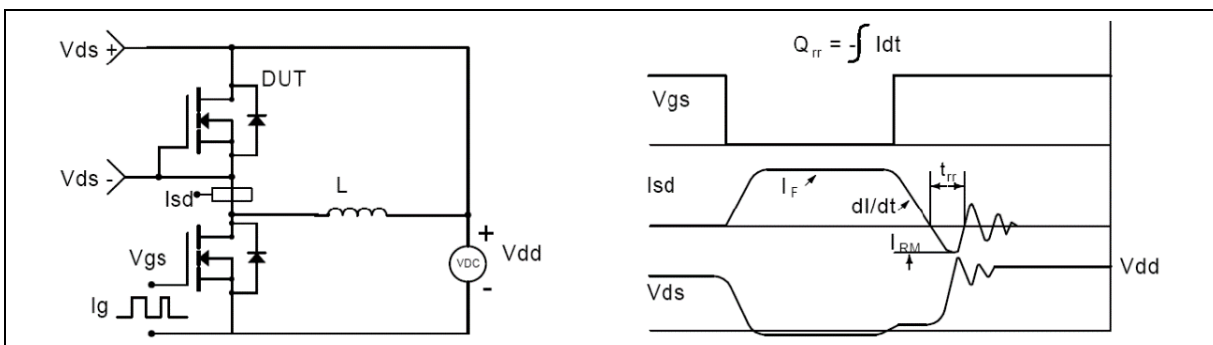
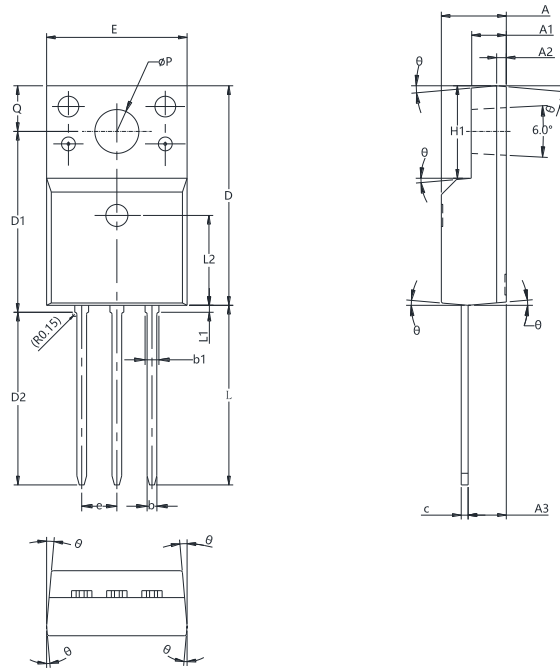


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.5	4.7	4.83
A1	2.34	2.54	2.74
A2	0.70 REF		
A3	2.56	2.76	2.93
b	0.6	-	0.8
b1	0.9	-	1.1
c	0.45	0.5	0.6
D	15.67	15.87	16.07
D1	12.87	13.07	13.27
D2	12.28	12.48	12.68
E	9.96	10.16	10.36
e	2.54 BSC		
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	-	-	0.85
L2	6.50 REF		
ΦP	3.08	3.18	3.28
Q	3.20	-	3.40
θ1	1°	3°	5°

Version: TO220F-NL-J package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO220F-NL-J	50	20	1000	5	5000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R125FF_NB	TO220F-NL	yes	yes	yes

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Revision History

Version	Revision History	Date
V1.0	Initial release	2025-10-15